

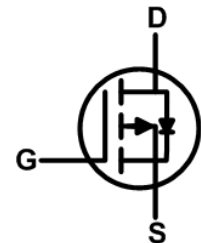
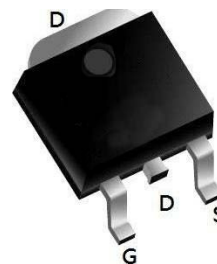
- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology


**Product Summary**

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
-20V	3.8mΩ	-80A

**Description**

The XXW80P02 is the high cell density trenched P-ch MOSFETs, which provide excellent R<sub>DS(on)</sub> and gate charge for most of the synchronous buck converter applications. The XXW80P02 meet the RoHS and Green Product requirement with full function reliability approved.

**TO252 Pin Configuration**

**Absolute Maximum Ratings (TA = 25°C, unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current	I <sub>D</sub>	T <sub>C</sub> =25°C	-80
		T <sub>C</sub> =100°C	-44
Pulsed Drain Current <sup>1</sup>	I <sub>DM</sub>	-280	A
Single Pulse Avalanche Energy <sup>2</sup>	E <sub>AS</sub>	80	mJ
Total Power Dissipation	P <sub>D</sub>	43.1	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient <sup>3</sup>	R <sub>θJA</sub>	65	°C/W
Thermal Resistance from Junction-to-Case	R <sub>θJC</sub>	2.9	°C/W

**Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	<b>V<sub>(BR)DSS</sub></b>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-20	-	-	V
Gate-body Leakage current	<b>I<sub>GSS</sub></b>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±12V	-	-	±100	nA
Zero Gate Voltage Drain Current	T <sub>J</sub> =25°C	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	-	-	-1	μA
	T <sub>J</sub> =100°C		-	-	-100	
Gate-Threshold Voltage	<b>V<sub>GS(th)</sub></b>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.4	-0.7	-1	V
Drain-Source On-Resistance <sup>4</sup>	<b>R<sub>DS(on)</sub></b>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A	-	3.8	5.2	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -10A	-	5	6.8	
Forward Transconductance <sup>4</sup>	<b>g<sub>fs</sub></b>	V <sub>DS</sub> = -4.5V, I <sub>D</sub> = -10A	-	56	-	S
<b>Dynamic Characteristics<sup>5</sup></b>						
Input Capacitance	<b>C<sub>iss</sub></b>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1MHz	-	4770	-	pF
Output Capacitance	<b>C<sub>oss</sub></b>		-	665	-	
Reverse Transfer Capacitance	<b>C<sub>rss</sub></b>		-	570	-	
Gate Resistance	<b>R<sub>g</sub></b>	f = 1MHz	-	9.6	-	Ω
<b>Switching Characteristics<sup>5</sup></b>						
Total Gate Charge	<b>Q<sub>g</sub></b>	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -10A	-	55	-	nC
Gate-Source Charge	<b>Q<sub>gs</sub></b>		-	5.2	-	
Gate-Drain Charge	<b>Q<sub>gd</sub></b>		-	10	-	
Turn-On Delay Time	<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = -4.5V, V <sub>DD</sub> = -10V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = -10A	-	22	-	ns
Rise Time	<b>t<sub>r</sub></b>		-	38	-	
Turn-Off Delay Time	<b>t<sub>d(off)</sub></b>		-	110	-	
Fall Time	<b>t<sub>f</sub></b>		-	62	-	
<b>Drain-Source Body Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	<b>V<sub>SD</sub></b>	I <sub>S</sub> = -10A, V <sub>GS</sub> = 0V	-	-	-1.2	V
Continuous Source Current	T <sub>C</sub> =25°C	<b>I<sub>S</sub></b>	-	-	-80	A

Note :

1. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C.
2. The EAS data shows Max. rating. The test condition is V<sub>DD</sub>= -25V, V<sub>GS</sub>= -10V, L= 0.4mH, I<sub>AS</sub>= -20A.
3. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

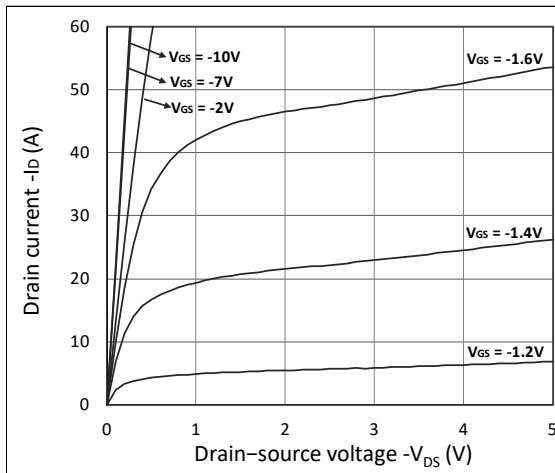
**Typical Characteristics**


Figure 1. Output Characteristics

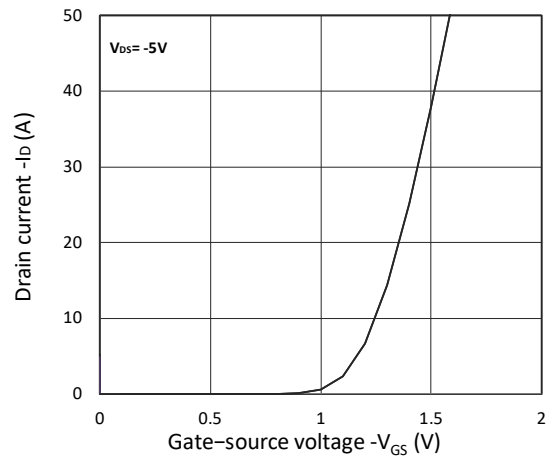


Figure 2. Transfer Characteristics

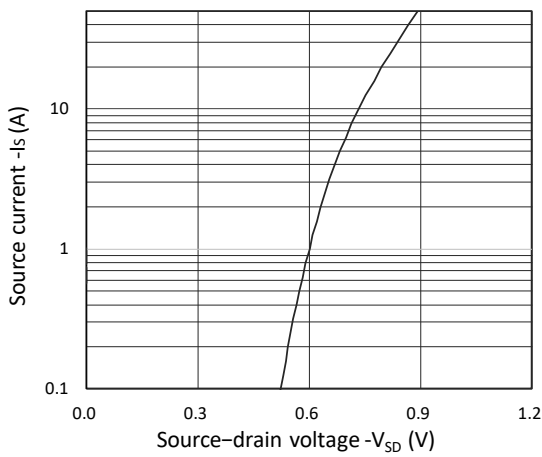
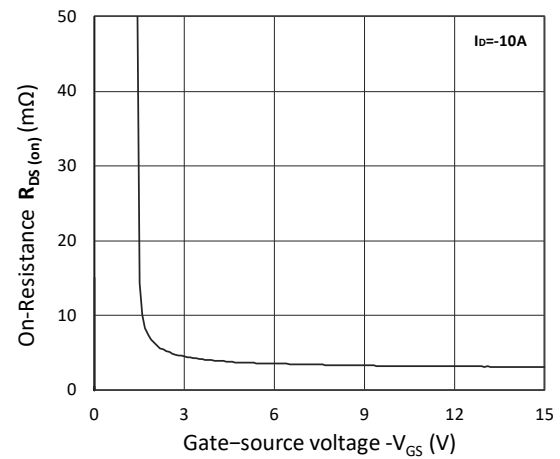
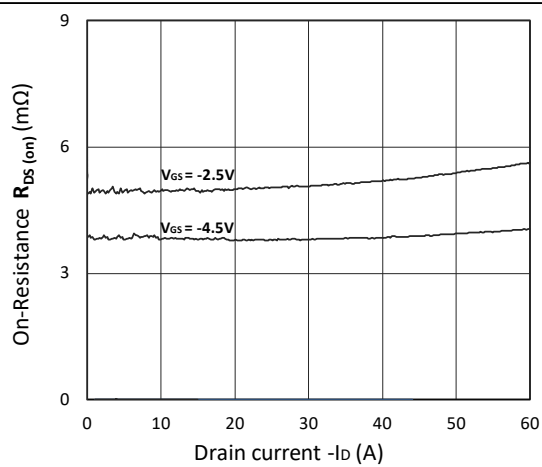
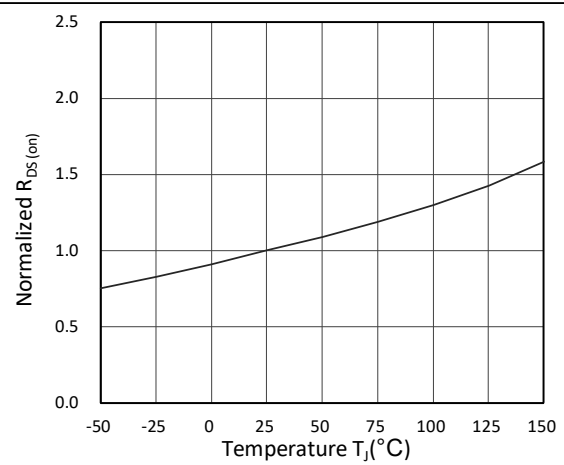


Figure 3. Forward Characteristics of Reverse


 Figure 4.  $R_{DS(ON)}$  vs.  $V_{GS}$ 

 Figure 5.  $R_{DS(ON)}$  vs.  $I_D$ 

 Figure 6. Normalized  $R_{DS(ON)}$  vs. Temperature

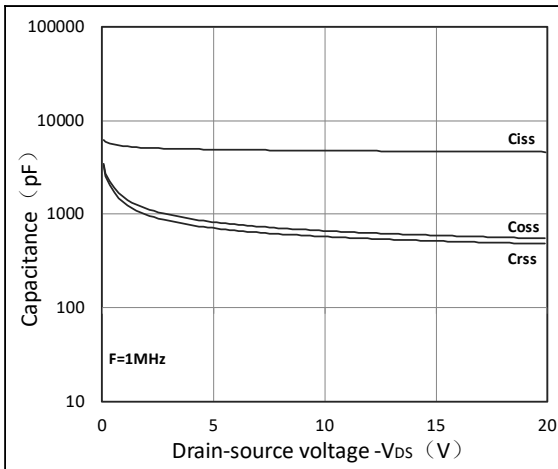


Figure 7. Capacitance Characteristics

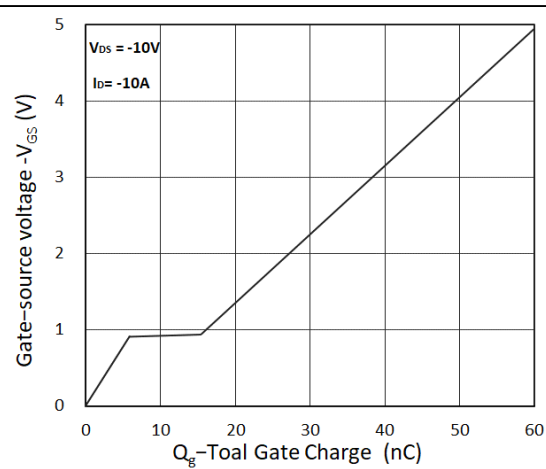


Figure 8. Gate Charge Characteristics

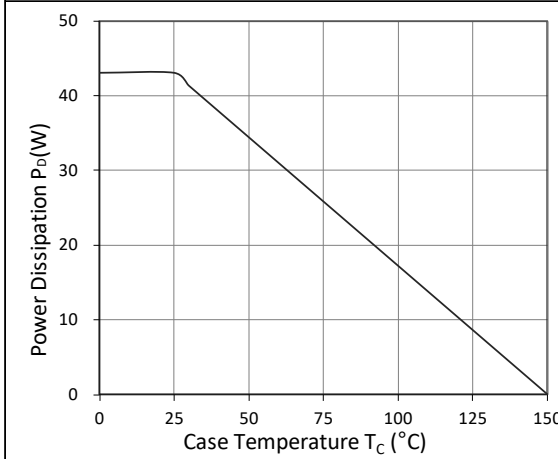


Figure 9. Power Dissipation

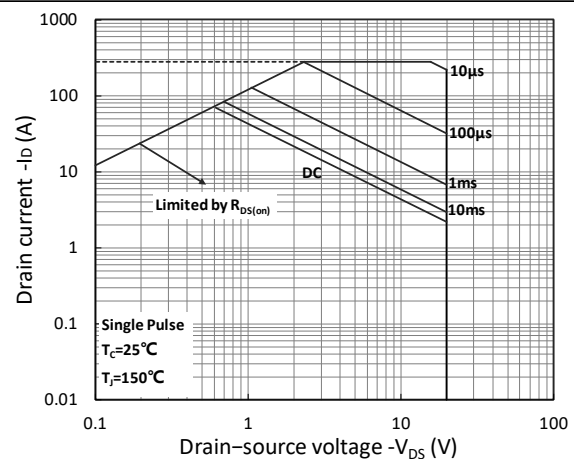


Figure 10. Safe Operating Area

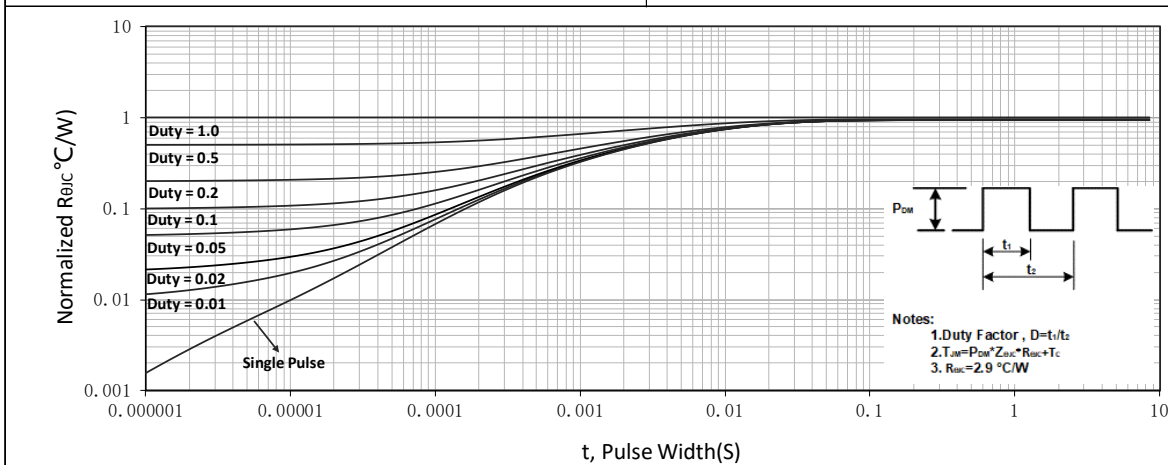
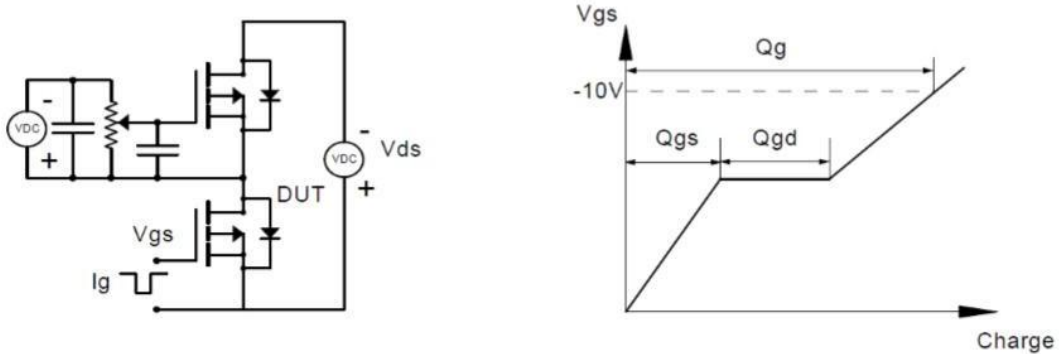
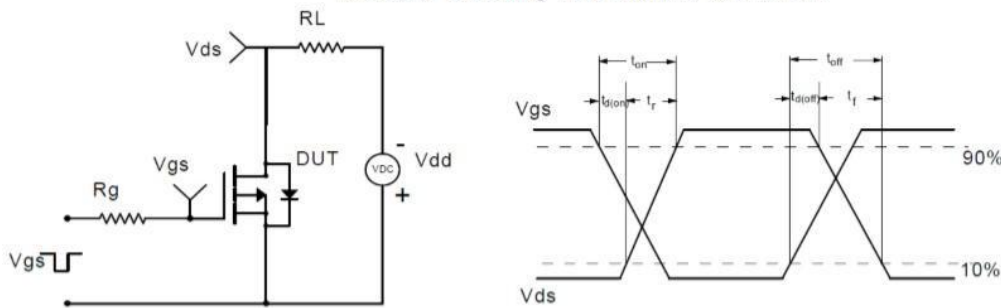
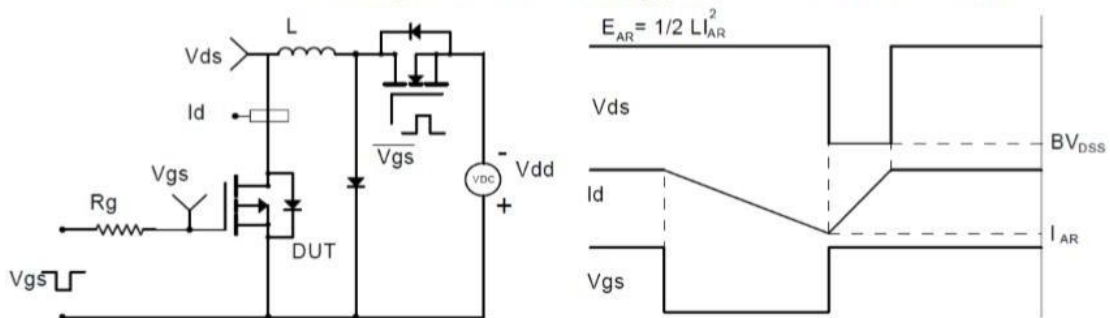
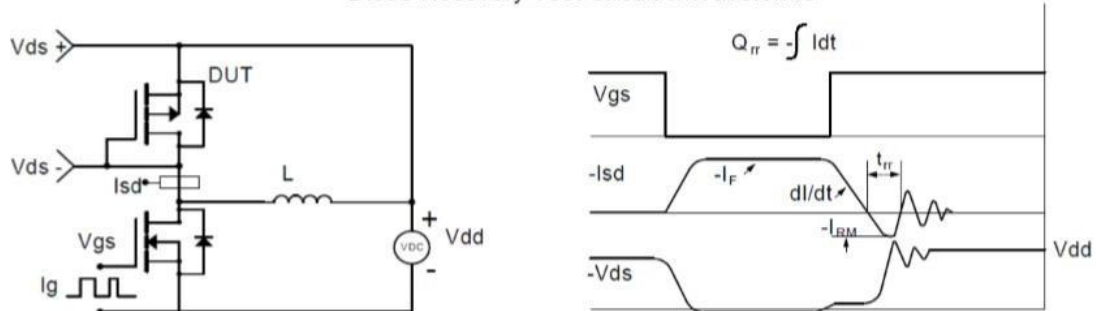
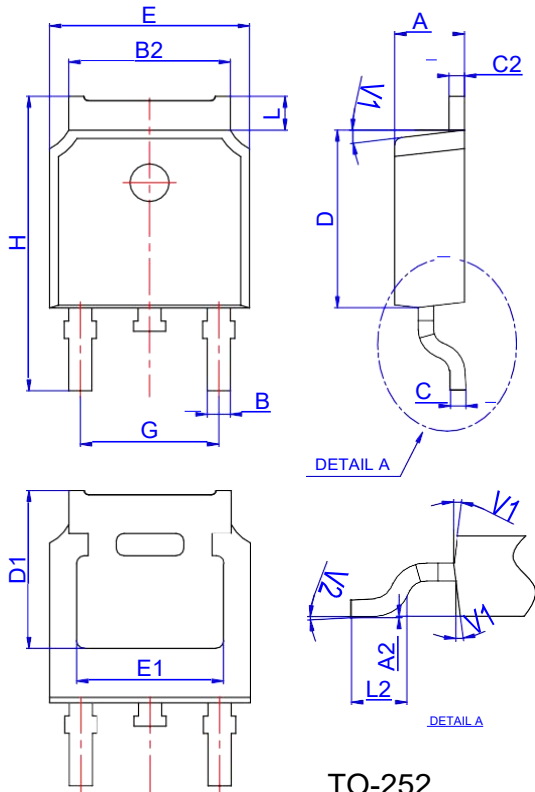
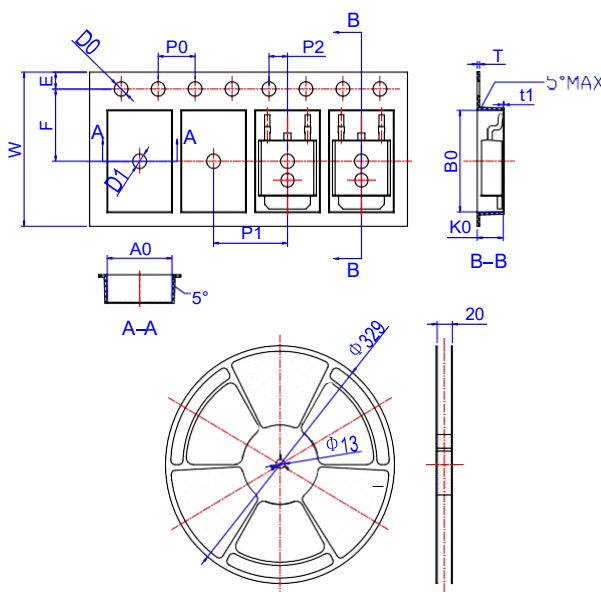


Figure 11. Normalized Maximum Transient Thermal Impedance

**Test Circuit**
**Gate Charge Test Circuit & Waveform**

**Resistive Switching Test Circuit & Waveforms**

**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**

**Diode Recovery Test Circuit & Waveforms**


**Package Mechanical Data-TO-252**


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

**Reel Specification-TO-252-4R**


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583